

To all our customers

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The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note : Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

DESCRIPTION

The M5M5V108DFP,VP,KV are a 1048576-bit CMOS static RAM organized as 131072 word by 8-bit which are fabricated using high-performance triple-polysilicon and double metal CMOS technology. The use of thin film transistor (TFT) load cells and CMOS periphery result in a high density and low power static RAM.

They are low standby current and low operation current and ideal for the battery back-up application.

The M5M5V108DVP,KV are packaged in a 32-pin thin small outline package which is a high reliability and high density surface mount device(SMD).

FEATURES

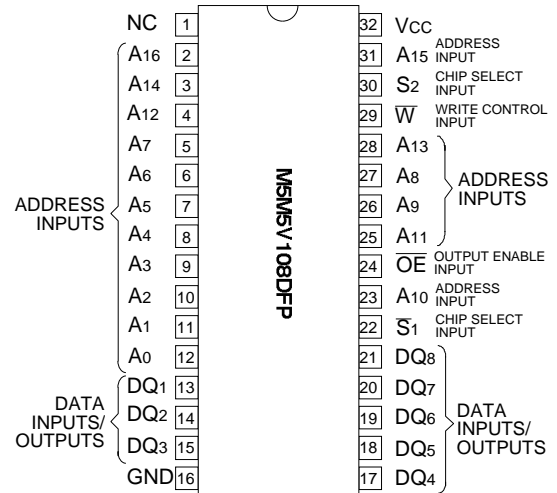
Type name	Access time (max)	Vcc	Power supply current	
			Active (1MHz) (max)	stand-by (max)
M5M5V108DFP,VP,KV-70H	70ns	2.7~3.6V	5mA	12 μ A

- Directly TTL compatible : All inputs and outputs
- Easy memory expansion and power down by \overline{S}_1, S_2
- Data hold on +2V power supply
- Three-state outputs : OR - tie capability
- \overline{OE} prevents data contention in the I/O bus
- Common data I/O
- Package

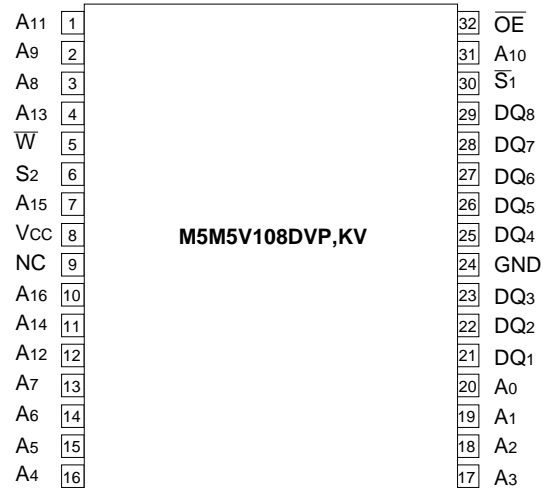
M5M5V108DFP 32pin 525mil SOP
 M5M5V108DVP,RV 32pin 8 X 20 mm² TSOP
 M5M5V108DKV,KR 32pin 8 X 13.4 mm² TSOP

APPLICATION

Small capacity memory units

PIN CONFIGURATION (TOP VIEW)

Outline 32P2M-A



Outline 32P3H-E(VP), 32P3K-B(KV)

NC : NO CONNECTION

FUNCTION

The operation mode of the M5M5V108D series are determined by a combination of the device control inputs $\overline{S}_1, S_2, \overline{W}$ and \overline{OE} .

Each mode is summarized in the function table.

A write cycle is executed whenever the low level \overline{W} overlaps with the low level \overline{S}_1 and the high level S_2 . The address must be set up before the write cycle and must be stable during the entire cycle. The data is latched into a cell on the trailing edge of \overline{W}, S_1 or S_2 , whichever occurs first, requiring the set-up and hold time relative to these edge to be maintained. The output enable input \overline{OE} directly controls the output stage. Setting the \overline{OE} at a high level, the output stage is in a high-impedance state, and the data bus contention problem in the write cycle is eliminated.

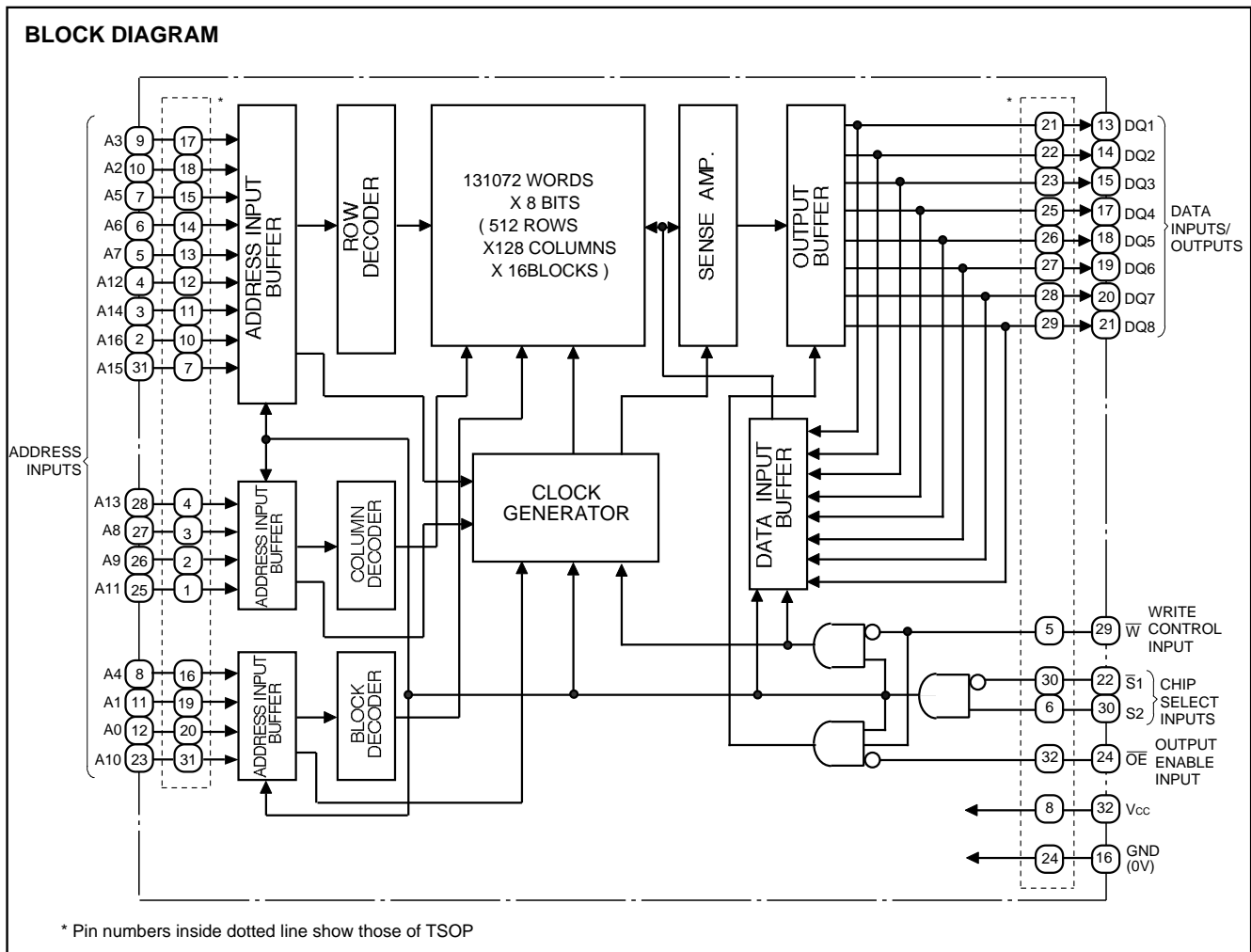
A read cycle is executed by setting \overline{W} at a high level and \overline{OE} at a low level while \overline{S}_1 and S_2 are in an active state ($\overline{S}_1=L, S_2=H$).

When setting \overline{S}_1 at a high level or S_2 at a low level, the chip are in a non-selectable mode in which both reading and writing are disabled. In this mode, the output stage is in a high-impedance state, allowing OR-tie with other chips and memory expansion by \overline{S}_1 and S_2 . The power supply current is reduced as low as the stand-by current which is specified as I_{CC3} or I_{CC4} , and the memory data can be held at +2V power supply, enabling battery back-up operation during power failure or power-down operation in the non-selected mode.

FUNCTION TABLE

\overline{S}_1	S_2	\overline{W}	\overline{OE}	Mode	DQ	I_{CC}
X	L	X	X	Non selection	High-impedance	Stand-by
H	X	X	X	Non selection	High-impedance	Stand-by
L	H	L	X	Write	Din	Active
L	H	H	L	Read	Dout	Active
L	H	H	H		High-impedance	Active

Note 1: "H" and "L" in this table mean V_{IH} and V_{IL} , respectively.
2: "X" in this table should be "H" or "L".



7th.July.2000 Ver. 1.1
MITSUBISHI LSIs
M5M5V108DFP,VP,KV -70H
1048576-BIT(131072-WORD BY 8-BIT)CMOS STATIC RAM

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V _{cc}	Supply voltage	With respect to GND	-0.3*~4.6	V
V _I	Input voltage		-0.3*~V _{cc} + 0.3 (Max 4.6)	V
V _O	Output voltage		0~V _{cc}	V
P _d	Power dissipation	T _a =25°C	700	mW
T _{opr}	Operating temperature		0~70	°C
T _{stg}	Storage temperature		-65~150	°C

* -3.0V in case of AC (Pulse width 30ns)

DC ELECTRICAL CHARACTERISTICS (T_a=0~70°C, V_{cc}=2.7~3.6V, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{IH}	High-level input voltage		2.0		V _{cc} + 0.3	V
V _{IL}	Low-level input voltage		-0.3*		0.6	V
V _{OH1}	High-level output voltage 1	I _{OH} = -0.5mA	2.4			V
V _{OH2}	High-level output voltage 2	I _{OH} = -0.05mA	V _{cc} - 0.5			V
V _{OL}	Low-level output voltage	I _{OL} = 2mA			0.4	V
I _I	Input current	V _I =0~V _{cc}			±1	µA
I _O	Output current in off-state	S ₁ =V _{IH} or S ₂ =V _{IL} or \overline{OE} =V _{IH} V _{I/O} =0~V _{cc}			±1	µA
I _{CC1}	Active supply current	S ₁ =V _{IL} , S ₂ =V _{IH} , other inputs=V _{IH} or V _{IL} Output-open(duty 100%)	70ns		35	
I _{CC2}	Active supply current		1MHz		5	
I _{CC3}	Stand-by current	1) S ₂ 0.2V other inputs=0~V _{cc} 2) S ₁ V _{cc} -0.2V, S ₂ V _{cc} -0.2V other inputs=0~V _{cc}	-H	~25°C	1.2	µA
				~40°C	3.6	
				~70°C	12	
I _{CC4}	Stand-by current	S ₁ =V _{IH} or S ₂ =V _{IL} , other inputs=0~V _{cc}			0.33	mA

* -3.0V in case of AC (Pulse width 30ns)

CAPACITANCE (T_a=0~70°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
C _I	Input capacitance	V _I =GND, V _I =25mVrms, f=1MHz			8	pF
C _O	Output capacitance	V _O =GND, V _O =25mVrms, f=1MHz			10	pF

Note 3: Direction for current flowing into an IC is positive (no mark).

4: Typical value is V_{cc} = 3V, T_a = 25°C

AC ELECTRICAL CHARACTERISTICS (Ta=0~70°C, unless otherwise noted)

(1) MEASUREMENT CONDITIONS

- VCC 2.7~3.6V
- Input pulse level VIH=2.2V, VIL=0.4V
- Input rise and fall time 5ns
- Reference level VOH=VOL=1.5V
- Output loads Fig.1, CL=30pF
 CL=5pF (for ten,tdis)
 Transition is measured ± 500mV from steady
 state voltage. (for ten,tdis)

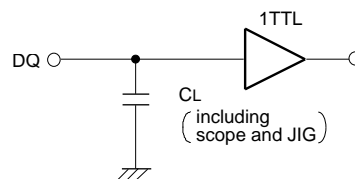


Fig.1 Output load

(2) READ CYCLE

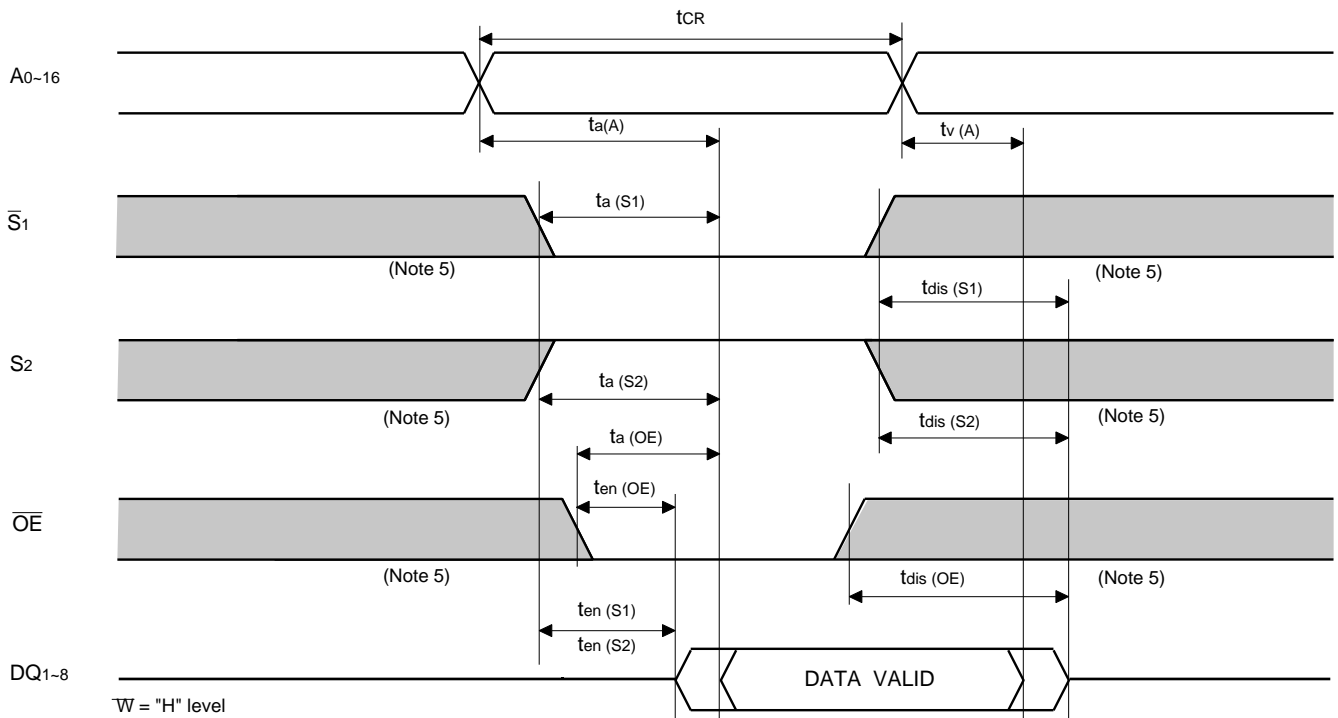
Symbol	Parameter	Limits		Unit
		-70H		
		Min	Max	
tCR	Read cycle time	70		ns
ta(A)	Address access time		70	ns
ta(S1)	Chip select 1 access time		70	ns
ta(S2)	Chip select 2 access time		70	ns
ta(OE)	Output enable access time		35	ns
tdis(S1)	Output disable time after S1 high		25	ns
tdis(S2)	Output disable time after S2 low		25	ns
tdis(OE)	Output disable time after OE high		25	ns
ten(S1)	Output enable time after S1 low	10		ns
ten(S2)	Output enable time after S2 high	10		ns
ten(OE)	Output enable time after OE low	5		ns
tV(A)	Data valid time after address	10		ns

(3) WRITE CYCLE

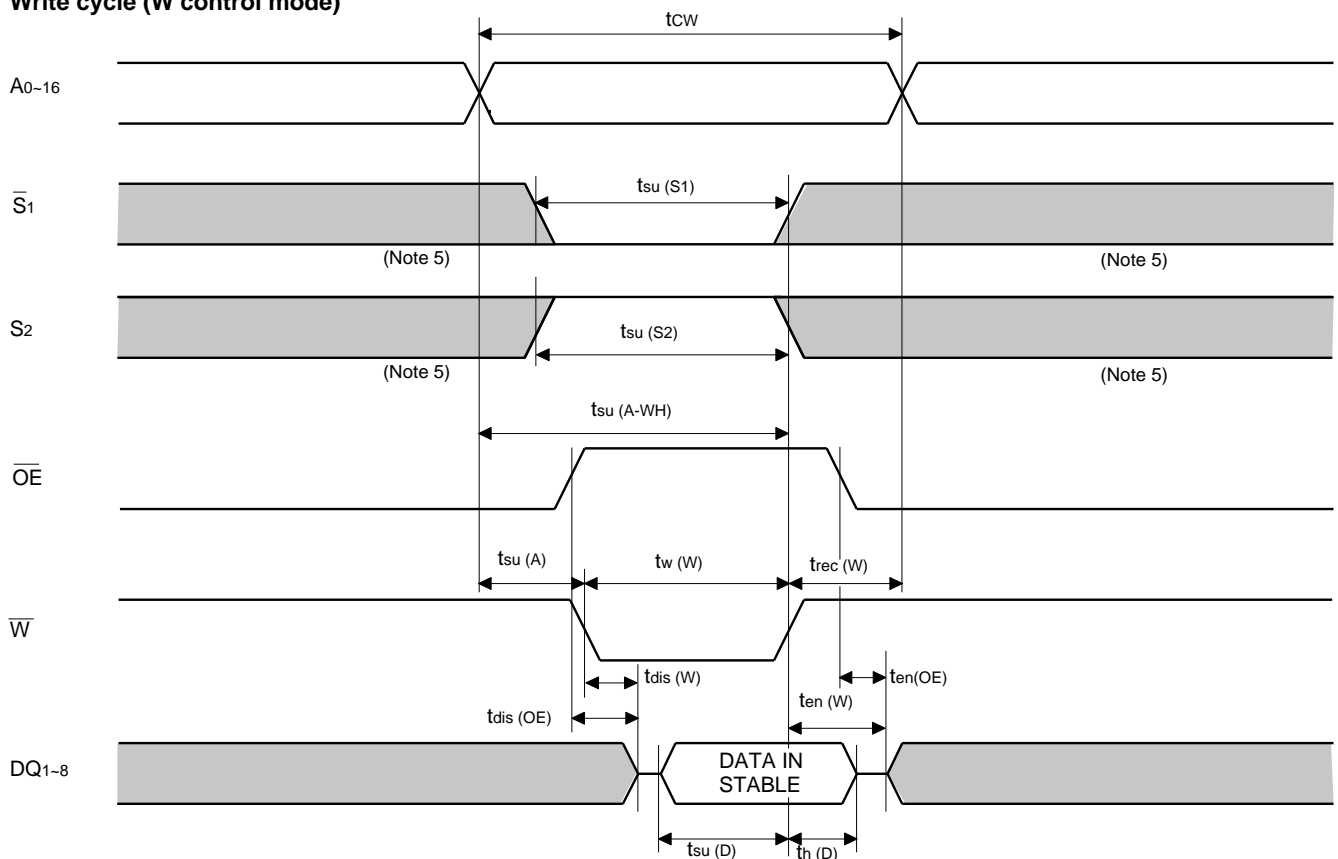
Symbol	Parameter	Limits		Unit
		-70H		
		Min	Max	
tCW	Write cycle time	70		ns
tW(W)	Write pulse width	55		ns
tsu(A)	Address setup time	0		ns
tsu(A-WH)	Address setup time with respect to W	65		ns
tsu(S1)	Chip select 1 setup time	65		ns
tsu(S2)	Chip select 2 setup time	65		ns
tsu(D)	Data setup time	30		ns
th(D)	Data hold time	0		ns
trec(W)	Write recovery time	0		ns
tdis(W)	Output disable time from W low		25	ns
tdis(OE)	Output disable time from OE high		25	ns
ten(W)	Output enable time from W high	5		ns
ten(OE)	Output enable time from OE low	5		ns

(4) TIMING DIAGRAMS

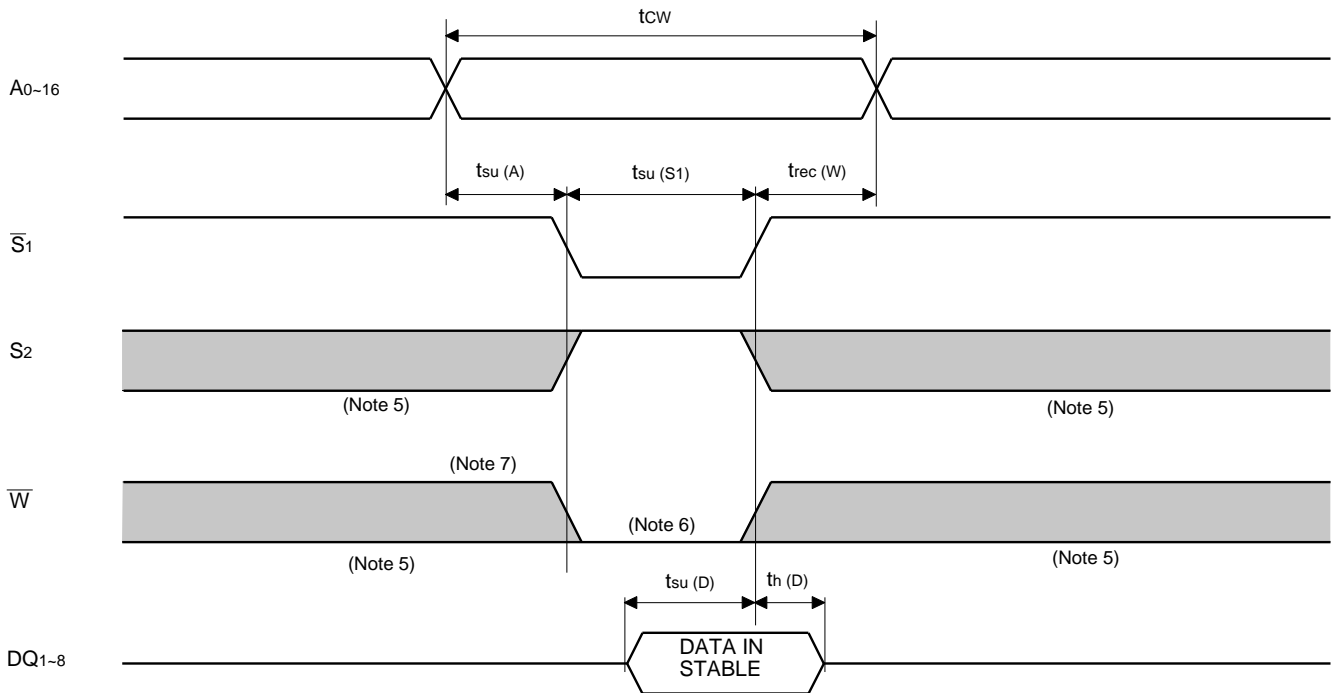
Read cycle



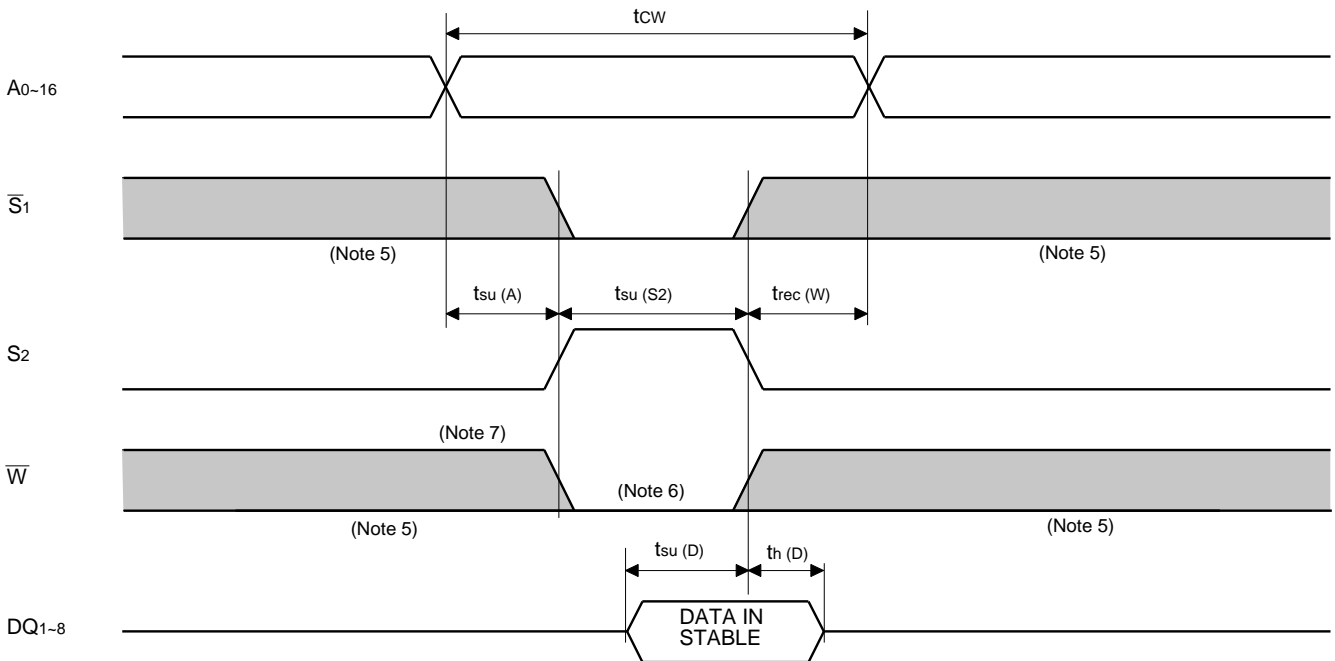
Write cycle (\bar{W} control mode)



Write cycle ($\overline{S1}$ control mode)



Write cycle (S2 control mode)



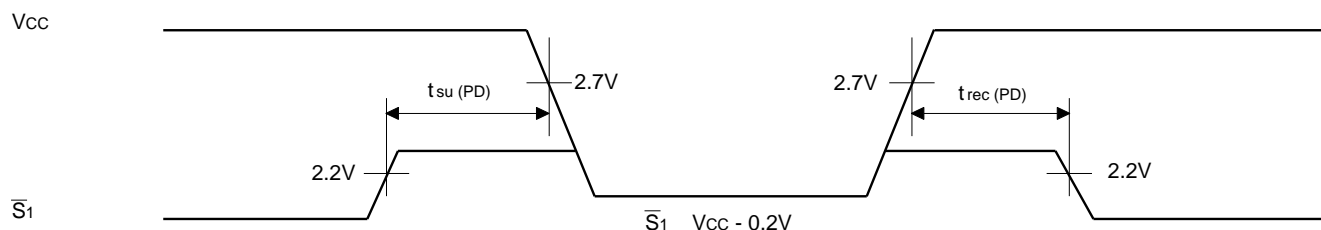
- Note 5: Hatching indicates the state is "don't care".
 6: Writing is executed while S2 high overlaps $\overline{S1}$ and \overline{W} low.
 7: When the falling edge of \overline{W} is simultaneously or prior to the falling edge of $\overline{S1}$ or rising edge of S2, the outputs are maintained in the high impedance state.
 8: Don't apply inverted phase signal externally when DQ pin is output mode.

POWER DOWN CHARACTERISTICS**(1) ELECTRICAL CHARACTERISTICS** (Ta=0~70°C, unless otherwise noted)

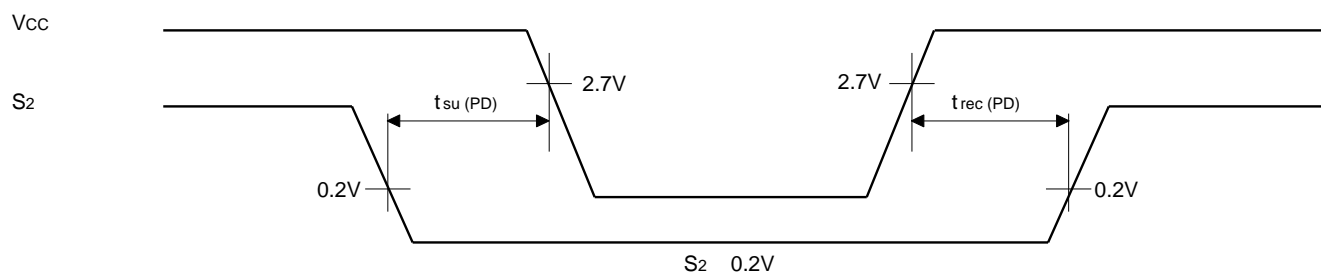
Symbol	Parameter	Test conditions	Limits			Unit	
			Min	Typ	Max		
V _{CC} (PD)	Power down supply voltage		2			V	
V _I (S1)	Chip select input $\overline{S1}$		2.0	V _{CC} (PD)		V	
V _I (S2)	Chip select input S2	2.7V V _{CC} (PD)			0.6	V	
		V _{CC} (PD)<2.7V			0.2	V	
I _{CC} (PD)	Power down supply current	V _{CC} = 3V 1) S2 0.2V, other inputs = 0~3V 2) $\overline{S1}$ V _{CC} -0.2V, S2 V _{CC} -0.2V other inputs = 0~3V	-H	~25°C		1	μA
				~40°C		3	
				~70°C		10	

(2) TIMING REQUIREMENTS (Ta=0~70°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
t _{su} (PD)	Power down set up time		0			ns
t _{rec} (PD)	Power down recovery time		5			ms

(3) POWER DOWN CHARACTERISTICS **$\overline{S1}$ control mode**

Note 9: On the power down mode by controlling $\overline{S1}$, the input level of S2 must be S2 = V_{CC} - 0.2V or S2 = 0.2V. The other pins(Address, I/O, \overline{WE} , \overline{OE}) can be in high impedance state.

S2 control mode

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